

TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

1SS337

ULTRA HIGH SPEED SWITCHING APPLICATION.

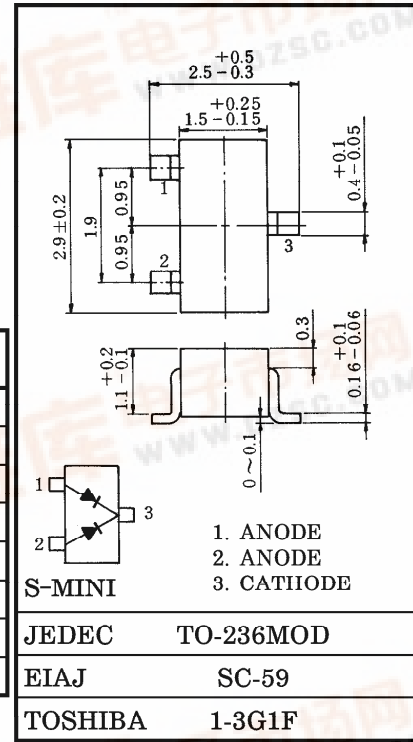
Unit in mm

- Small Package : SC-59
- Low Forward Voltage : $V_{F(3)} = 0.88V$ (Typ.)
- Fast Reverse Recovery Time : $t_{rr} = 6ns$ (Typ.)
- Small Total Capacitance : $C_T = 1.6pF$ (Typ.)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Maximum (Peak) Forward Current	I_{FM}	600*	mA
Average Forward Current	I_O	200*	mA
Surge Current (10ms)	I_{FSM}	6*	A
Power Dissipation	P	150	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55~150	$^\circ C$

* Unit Rating. Total Rating=Unit Rating×1.5



Weight : 0.012g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	$I_F = 10mA$	—	0.66	—	V
	$V_{F(2)}$	$I_F = 100mA$	—	0.80	—	
	$V_{F(3)}$	$I_F = 200mA$	—	0.88	1.20	
Reverse Current	$I_{R(1)}$	$V_R = 30V$	—	—	0.25	μA
	$I_{R(2)}$	$V_R = 80V$	—	—	0.50	
Total Capacitance	C_T	$V_R = 0, f = 1MHz$	—	1.6	—	pF
Reverse Recovery Time	t_{rr}	$I_F = 30mA, Fig.1$	—	6	20	ns

Fig.1 REVERSE RECOVERY TIME (t_{rr}) TEST CIRCUIT

